

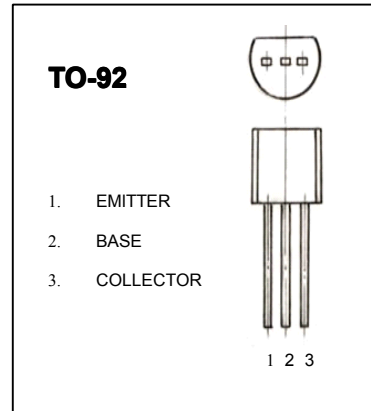
TO-92 Plastic-Encapsulate Transistors

2N5401 TRANSISTOR (PNP)
FEATURE

- Switching and amplification in high voltage
- Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.160v)

MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-160	V
V _{CE0}	Collector-Emitter Voltage	-150	V
V _{EB0}	Emitter-Base Voltage	-5	V
I _c	Collector Current -Continuous	-0.6	A
P _c	Collector Power Dissipation	0.625	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _c = -100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c = -1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _c =0	-5			V
Collector cut-off current	I _{cBO}	V _{CB} = -120 V, I _E =0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _c =0			-50	nA
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _c =-1 mA	80			
	h _{FE(2)}	V _{CE} = -5V, I _c = -10 mA	60		240	
	h _{FE(3)}	V _{CE} = -5V, I _c =-50 mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c = -50mA, I _B = -5 mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c = -50mA, I _B = -5 mA			-1	V
Transition frequency	f _T	V _{CE} =-5V, I _c =-10mA f=30MHz	100		300	MHz

Typical Characteristics

2N5401

